L Number	Hits	Search Text	DB	Time stamp
3	1	1997-282330.NRAN.	DERWENT	2004/05/27 09:03
11	6	6099711.URPN.	USPAT	2004/05/27 09:03
12	2	6099711.URPN. and (iron or fe!)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/27 09:06
13	6	6099711.URPN.	USPAT	2004/05/27 09:05
14	1	"5186811".PN.	USPAT	2004/05/27 09:05
20	767	205/123,157.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/27 09:07
21	78	205/123,157.ccls. and (iron or fe!)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/27 09:20
22	59	(205/123,157.ccls. and (iron or fe!)) and (copper or cu!)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/27 09:07
23	296	205/101.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/27 09:28
24	86	205/101.ccls. and (iron or fe!)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/27 09:28
25	13	(205/101.ccls. and (iron or fe!)) and (semiconductor or silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/27 09:28
26	203	205/103.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/27 09:28
28	10	(205/103.ccls. and (iron or fe!)) and (semiconductor or silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/27 09:32

27	37	205/103.ccls. and (iron or fe!)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/27 09:30
-	1187	205/$.ccls. and (puls$3 with current)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/11 14:51
-	566	(205/$.ccls. and (puls$3 with current)) and copper	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/11 14:50
-	1232	205/$.ccls. and (puls$3 with (current or revers$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/11 14:51
-	8136	205/$.ccls. and copper	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/11 14:52
-	2472	205/$.ccls. and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/11 14:52
-	189	(205/$.ccls. and (puls$3 with (current or revers$3))) and (205/$.ccls. and copper) and (205/$.ccls. and semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/11 14:52
-	150	((205/$.ccls. and (puls$3 with (current or revers$3))) and (205/$.ccls. and copper) and (205/$.ccls. and semiconductor)) and (recess or trench or via or hole)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/11 15:01
-	22	(((205/$.ccls. and (puls$3 with (current or revers$3))) and (205/$.ccls. and copper) and (205/$.ccls. and semiconductor)) and (recess or trench or via or hole)) and ((inert or noble or titanium) near (anode or electrode or counterelectrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 09:20
-	2	"6432293"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/11 15:24
-	1	2000-642506.NRAN.	DERWENT	2003/06/11 15:22

-	61	205/$.ccls. and damascene and puls$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/11 16:06
-	258	205/$.ccls. and ((cathodic or plating or forward) adj (current or pulse)) and ((anodic or polishing or etching or dissolution) adj (current or pulse))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/11 16:09
-	43	(205/$.ccls. and ((cathodic or plating or forward) adj (current or pulse)) and ((anodic or polishing or etching or dissolution) adj (current or pulse))) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/11 16:09
-	2	gb-2214520-$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 08:47
-	35091	205/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 09:03
-	2587	205/$.ccls. and (semiconductor or (silicon adj wafer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 09:19
-	1589	(205/$.ccls. and (semiconductor or (silicon adj wafer))) and (recess or trench or via or hole)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 09:20
-	918	((205/$.ccls. and (semiconductor or (silicon adj wafer))) and (recess or trench or via or hole)) and copper	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 09:20
-	286	((205/$.ccls. and (semiconductor or (silicon adj wafer))) and (recess or trench or via or hole)) and (copper near (electroplat$4 or electrochem$6 or electroly$6))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 09:31
-	48	(((205/$.ccls. and (semiconductor or (silicon adj wafer))) and (recess or trench or via or hole)) and (copper near (electroplat$4 or electrochem$6 or electroly$6))) and (iron or "fe(II)" or "fe(III)" or fe! or ((ferric or ferrous) adj ion))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 09:31

-	336	(205/$.ccls. and (semiconductor or (silicon adj wafer))) and (copper near (electroplat$4 or electrochem$6 or electroly$6))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 09:31
-	63	((205/$.ccls. and (semiconductor or (silicon adj wafer))) and (copper near (electroplat$4 or electrochem$6 or electroly$6))) and (iron or "fe(II)" or "fe(III)" or fe! or ((ferric or ferrous) adj ion))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 09:31
-	15	(((205/$.ccls. and (semiconductor or (silicon adj wafer))) and (copper near (electroplat$4 or electrochem$6 or electroly$6))) and (iron or "fe(II)" or "fe(III)" or fe! or ((ferric or ferrous) adj ion))) not ((((205/$.ccls. and (semiconductor or (silicon adj wafer))) and (recess or trench or via or hole)) and (copper near (electroplat$4 or electrochem$6 or electroly$6)) and (iron or "fe(II)" or "fe(III)" or fe! or ((ferric or ferrous) adj ion)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 09:34
-	782	205/291-298.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 09:34
-	118	205/291-298.ccls. and (iron or fe! or ferrous or ferric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 09:34
-	106	205/291-298.ccls. and (semiconductor or silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 09:35
-	28	(205/291-298.ccls. and (iron or fe! or ferrous or ferric)) and (205/291-298.ccls. and (semiconductor or silicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 09:37
-	2	6099711.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 09:38
-	9	"6099711"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 09:38
-	1	1997-282330.NRAN.	DERWENT	2003/06/12 09:38

-	3205	205/101,102,103,104,118,122,123,157,183,220,221,291,29...	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 10:50
-	505	205/101,102,103,104,118,122,123,157,183,220,221,291,29... and semiconductor and (recess or trench or via or hole)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 10:51
-	549	205/101,102,103,104,118,122,123,157,183,220,221,291,29... and semiconductor and (recess or trench or via or hole or opening)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 10:51
-	391	(205/101,102,103,104,118,122,123,157,183,220,221,291,298... and semiconductor and (recess or trench or via or hole or opening)) and copper	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 10:51
-	220	((205/101,102,103,104,118,122,123,157,183,220,221,291,29... and semiconductor and (recess or trench or via or hole or opening)) and copper) and ((seed or barrier) near layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 10:52
-	69	(((205/101,102,103,104,118,122,123,157,183,220,221,291,29... and semiconductor and (recess or trench or via or hole or opening)) and copper) and ((seed or barrier) near layer)) and puls$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 10:52
-	69	(((205/101,102,103,104,118,122,123,157,183,220,221,291,29... and semiconductor and (recess or trench or via or hole or opening)) and copper) and ((seed or barrier) near layer)) and puls$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 12:06
-	44	((((205/101,102,103,104,118,122,123,157,183,220,221,29... and semiconductor and (recess or trench or via or hole or opening)) and copper) and ((seed or barrier) near layer)) and puls$5) and ((semiconductor or silicon) with (circuit))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 12:09
-	9	((((205/101,102,103,104,118,122,123,157,183,220,221,29... and semiconductor and (recess or trench or via or hole or opening)) and copper) and ((seed or barrier) near layer)) and puls$5) and ((semiconductor or silicon) with (circuit adj board))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 14:18
-	1	de-4344387-a1.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 14:22
-	1	1995-232640.NRAN.	DERWENT	2003/06/12 14:20

-	9	"5976341"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/12 14:22
-	0	1997wo-de19206.ap,prai.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/14 09:17
-	2	6099711.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/14 09:24
-	1	1997-282330.NRAN.	DERWENT	2004/01/14 09:18
-	2	5893966.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/14 09:24
-	1	5893966.pn. and (semiconductor with circuit)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/14 09:24